

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP731, TLP732

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
SOLID STATE RELAY
SWITCHING POWER SUPPLY

The TOSHIBA TLP731 and TLP732 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

TLP732 is no-base internal connection for high-EMI environments.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
Rank GB : 100% (Min.)
- UL Recognized : UL1577, File No. E67349
- BSI Approved : BS EN60065 : 1994
Certificate No. 6617
BS EN60950 : 1992
Certificate No. 7366

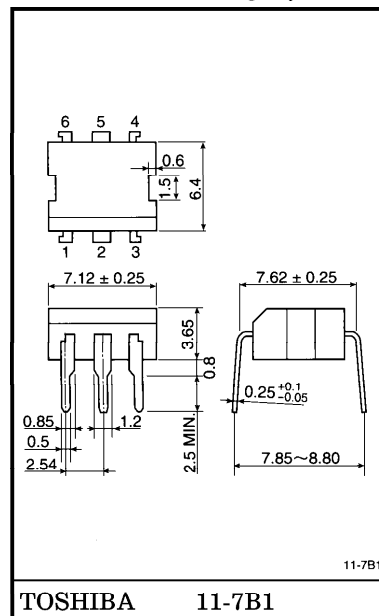
Isolation Voltage : 4000V_{rms} (Min.)

- Option (D4) type
VDE Approved : DIN VDE0884 / 08.87,
Certificate No. 65640
Maximum Operating Insulation Voltage : 630V_{PK}
Highest Permissible Over Voltage : 6000V_{PK}

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- | | 7.62mm pitch
standard type | 10.16mm pitch
(LF2) type |
|----------------------|-------------------------------|-----------------------------|
| ● Creepage Distance | : 7.0mm (Min.) | : 8.0mm (Min.) |
| Clearance | : 7.0mm (Min.) | : 8.0mm (Min.) |
| Insulation Thickness | : 0.5mm (Min.) | : 0.5mm (Min.) |

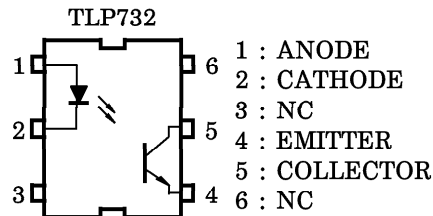
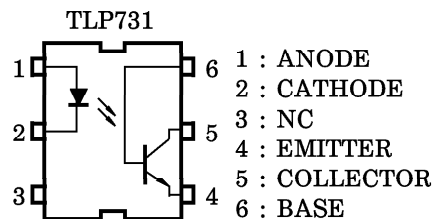
Unit in mm



TOSHIBA 11-7B1

Weight : 0.35g

PIN CONFIGURATIONS (TOP VIEW)



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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I_F	60	mA
	Forward Current Derating (Ta ≥ 39°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak Forward Current (100µs pulse, 100pps)	I_{FP}	1	A
	Power Dissipation	P_D	100	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_D / ^\circ\text{C}$	-1.0	mW / °C
	Reverse Voltage	V_R	5	V
	Junction Temperature	T_j	125	°C
DETECTOR	Collector-Emitter Voltage	V_{CEO}	55	V
	Collector-Base Voltage (TLP731)	V_{CBO}	80	V
	Emitter-Collector Voltage	V_{ECO}	7	V
	Emitter-Base Voltage (TLP731)	V_{EBO}	7	V
	Collector Current	I_C	50	mA
	Power Dissipation	P_C	150	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / °C
	Junction Temperature	T_j	125	°C
Storage Temperature Range		T_{stg}	-55~125	°C
Operating Temperature Range		T_{opr}	-55~100	°C
Lead Soldering Temperature (10s)		T_{sol}	260	°C
Total Package Power Dissipation		P_T	250	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.5	mW / °C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%)		BV_S	4000	V_{rms}

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	5	24	V
Forward Current	I_F	—	16	25	mA
Collector Current	I_C	—	1	10	mA
Operating Temperature	T_{opr}	-25	—	85	°C

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to foreign exchange and foreign trade laws.
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- The information contained herein is subject to change without notice.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V	
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA	
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF	
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V	
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V	
	Collector-Base Breakdown Voltage (TLP731)	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V	
	Emitter-Base Breakdown Voltage (TLP731)	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V	
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	$V_{CE} = 24\text{V}$	—	10	100	nA
				$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Collector Dark Current (TLP731)	I_{CER}	$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	μA	
	Collector Dark Current (TLP731)	I_{CBO}	$V_{CB} = 10\text{V}$	—	0.1	—	nA	
	DC Forward Current Gain (TLP731)	h_{FE}	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	400	—	—	
Capacitance Collector to Emitter	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF		

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F(\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Base Photo-Current (TLP731)	I_{PB}	$I_F = 5\text{mA}, V_{CB} = 5\text{V}$	—	10	—	μA
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C _S	V _S =0, f=1MHz	—	0.8	—	pF
Isolation Resistance	R _S	V _S =500V	1×10 ¹²	10 ¹⁴	—	Ω
Isolation Voltage	BV _S	AC, 1 minute	4000	—	—	V _{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t _r	V _{CC} =10V, I _C =2mA R _L =100Ω	—	2	—	μs
Fall Time	t _f		—	3	—	
Turn-on Time	t _{on}		—	3	10	
Turn-off Time	t _{off}		—	3	10	
Turn-on Time	t _{ON}	R _L =1.9kΩ (Fig.1)	—	2	—	μs
Storage Time	t _s	R _{BE} =OPEN	—	15	—	
Turn-off Time	t _{OFF}	V _{CC} =5V, I _F =16mA	—	25	—	
Turn-on Time	t _{ON}	R _L =1.9kΩ (Fig.1)	—	2	—	μs
Storage Time	t _s	R _{BE} =220kΩ (TLP731)	—	12	—	
Turn-off Time	t _{OFF}	V _{CC} =5V, I _F =16mA	—	20	—	

Fig. 1 SWITCHING TIME TEST CIRCUIT

